

TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

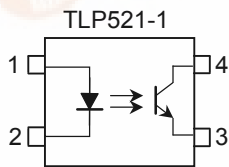
TLP521-1, TLP521-2, TLP521-4

Programmable Controllers
AC/DC-Input Module
Solid State Relay

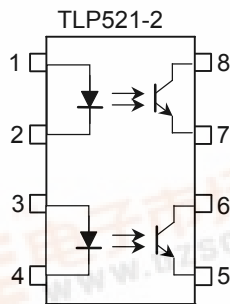
The TOSHIBA TLP521-1, -2 and -4 consist of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode. The TLP521-2 offers two isolated channels in an eight lead plastic DIP package, while the TLP521-4 provides four isolated channels in a sixteen plastic DIP package.

- Collector-emitter voltage: 55 V (min)
- Current transfer ratio: 50% (min)
Rank GB: 100% (min)
- Isolation voltage: 2500 Vrms (min)
- UL recognized
made in Japan: UL1577, file No. E67349
made in Thailand: UL1577, file No. E152349

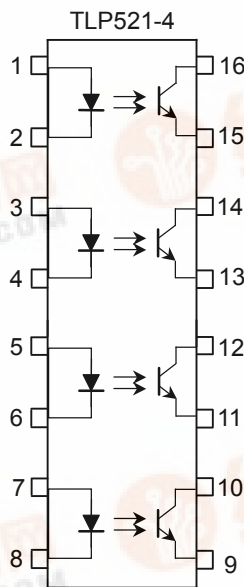
Pin Configurations (top view)



1 : Anode
2 : Cathode
3 : Emitter
4 : Collector

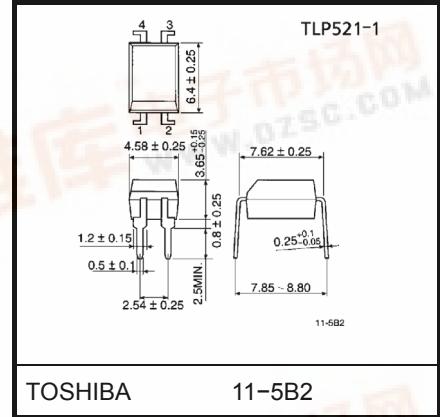


1, 3 : Anode
2, 4 : Cathode
5, 7 : Emitter
6, 8 : Collector



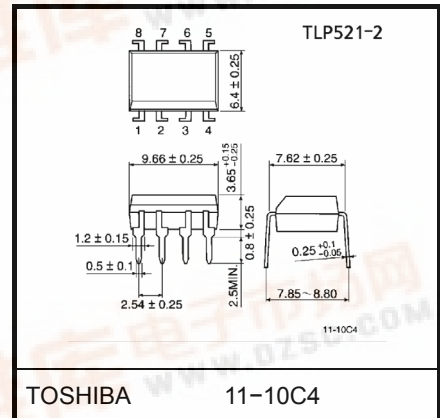
1, 3, 5, 7 : Anode
2, 4, 6, 8 : Cathode
9, 11, 13, 15 : Emitter
10, 12, 14, 16 : Collector

Unit in mm



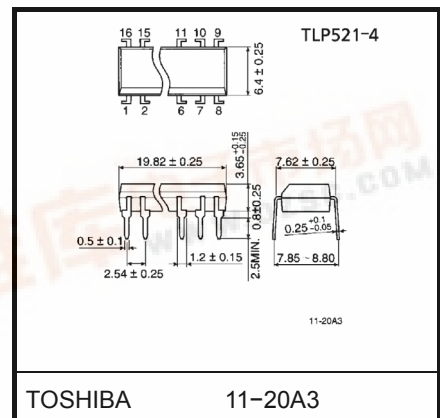
TOSHIBA 11-5B2

Weight: 0.26 g



TOSHIBA 11-10C4

Weight: 0.54 g



TOSHIBA 11-20A3

Weight: 1.1 g

Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating		Unit	
		TLP521-1	TLP521-2 TLP521-4		
LED	Forward current	I _F	70	50	mA
	Forward current derating	ΔI _F /°C	-0.93 (Ta ≥ 50°C)	-0.5 (Ta ≥ 25°C)	mA /°C
	Pulse forward current	I _{FP}	1 (100μ pulse, 100pps)		A
	Reverse voltage	V _R	5		V
	Junction temperature	T _j	125		°C
Detector	Collector-emitter voltage	V _{CEO}	55		V
	Emitter-collector voltage	V _{ECO}	7		V
	Collector current	I _C	50		mA
	Collector power dissipation (1 circuit)	P _C	150	100	mW
	Collector power dissipation derating (1 circuit Ta ≥ 25°C)	ΔP _C /°C	-1.5	-1.0	mW /°C
	Junction temperature	T _j	125		°C
Storage temperature range	T _{stg}	-55~125		°C	
Operating temperature range	T _{opr}	-55~100		°C	
Lead soldering temperature	T _{sol}	260 (10 s)		°C	
Total package power dissipation	P _T	250	150	mW	
Total package power dissipation derating (Ta ≥ 25°C)	ΔP _T /°C	-2.5	-1.5	mW /°C	
Isolation voltage	BV _S	2500 (AC, 1min., R.H. ≤ 60%) (Note 1)		V _{rms}	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Device considered a two terminal device: LED side pins shorted together and detector side pins shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min	Typ.	Max	Unit
Supply voltage	V _{CC}	—	5	24	V
Forward current	I _F	—	16	25	mA
Collector current	I _C	—	1	10	mA
Operating temperature	T _{opr}	-25	—	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Type	Classi- fication (*1)	Current Transfer Ratio (%) (I_C / I_F)		Marking Of Classification
		$I_F = 5\text{mA}, V_{CE} = 5\text{V}, T_a = 25^\circ\text{C}$		
		Min	Max	
TLP521	A	50	600	Blank, Y, Y [■] , G, G [■] , B, B [■] , GB
	Rank Y	50	150	Y, Y [■]
	Rank GR	100	300	G, G [■]
	Rank BL	200	600	B, B [■]
	Rank GB	100	600	G, G [■] , B, B [■] , GB
TLP521-2 TLP521-4	A	50	600	Blank, GR, BL, GB
	Rank GB	100	600	GR, BL, GB

*1: Ex. rank GB: TLP521-1 (GB)

(Note): Application type name for certification test, please use standard product type name, i.e.
TLP521-1 (GB): TLP521-1, TLP521-2 (GB): TLP521-2

Individual Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
LED	Forward voltage	V_F	$I_F = 10 \text{ mA}$	1.0	1.15	1.3	V
	Reverse current	I_R	$V_R = 5 \text{ V}$	—	—	10	μA
	Capacitance	C_T	$V = 0, f = 1 \text{ MHz}$	—	30	—	pF
Detector	Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 0.5 \text{ mA}$	55	—	—	V
	Emitter-collector breakdown voltage	$V_{(BR)ECO}$	$I_E = 0.1 \text{ mA}$	7	—	—	V
	Collector dark current	I_{CEO}	$V_{CE} = 24 \text{ V}$	—	10	100	nA
			$V_{CE} = 24 \text{ V}, T_a = 85^\circ\text{C}$	—	2	50	μA
Capacitance (collector to emitter)	C_{CE}	$V = 0, f = 1 \text{ MHz}$	—	10	—	pF	

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Current transfer ratio	I_C / I_F	$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$ Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	$I_C / I_F (\text{sat})$	$I_F = 1 \text{ mA}, V_{CE} = 0.4 \text{ V}$ Rank GB	—	60	—	%
			30	—	—	
Collector-emitter saturation voltage	$V_{CE} (\text{sat})$	$I_C = 2.4 \text{ mA}, I_F = 8 \text{ mA}$	—	—	0.4	V
		$I_C = 0.2 \text{ mA}, I_F = 1 \text{ mA}$ Rank GB	—	0.2	—	
			—	—	0.4	

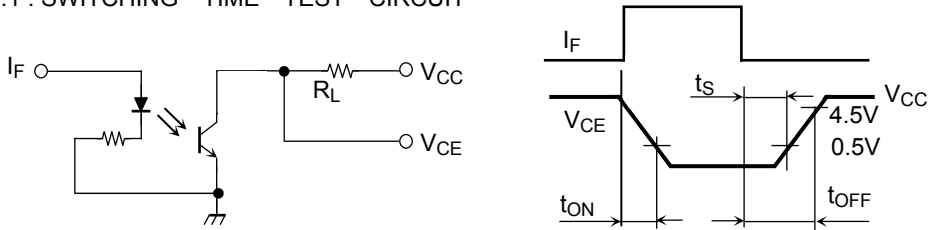
Isolation Characteristics (Ta = 25°C)

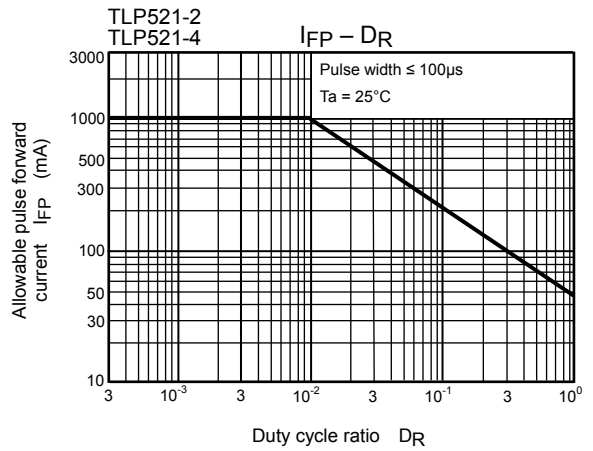
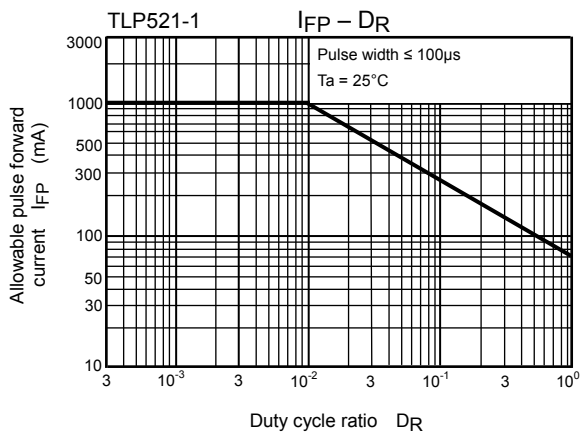
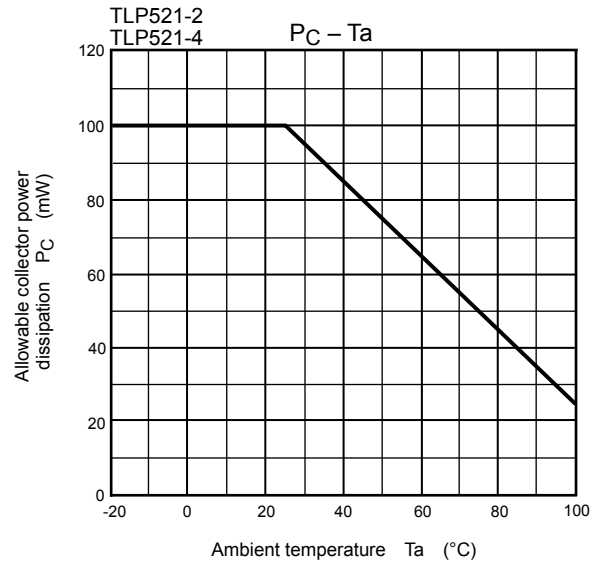
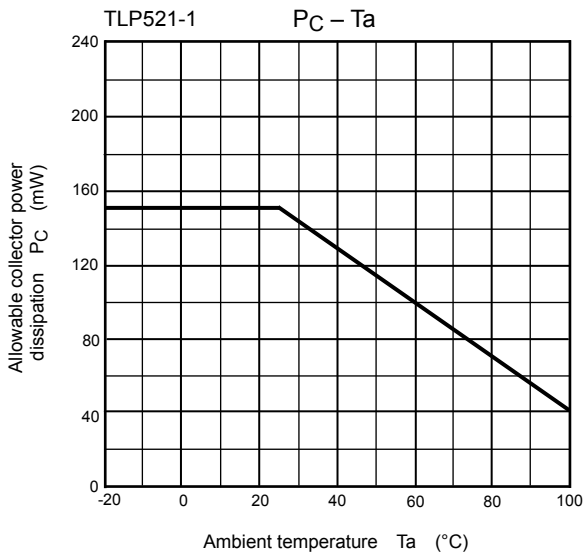
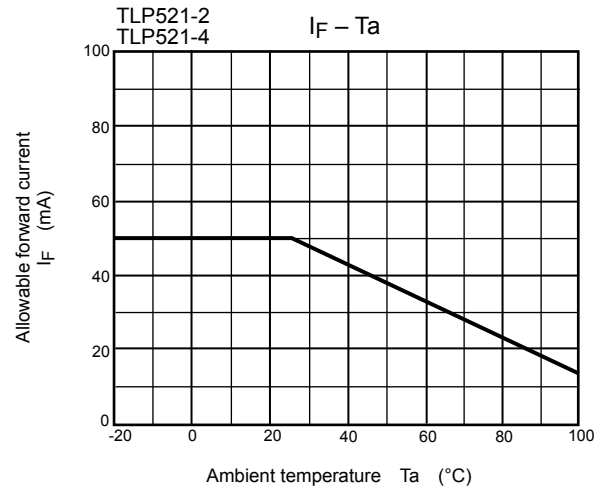
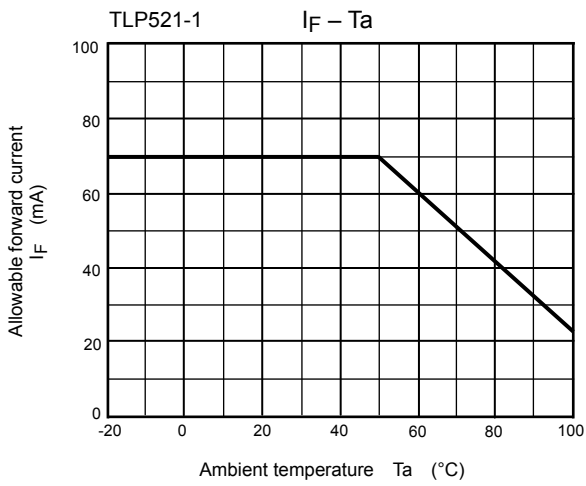
Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Capacitance (input to output)	C_S	$V_S = 0, f = 1 \text{ MHz}$	—	0.8	—	pF
Isolation resistance	R_S	$V_S = 500 \text{ V}, \text{R.H.} \leq 60\%$	—	10^{11}	—	Ω
Isolation voltage	BV_S	AC, 1 minute	2500	—	—	Vrms
		AC, 1 second, in oil	—	5000	—	
		DC, 1 minute, in oil	—	5000	—	Vdc

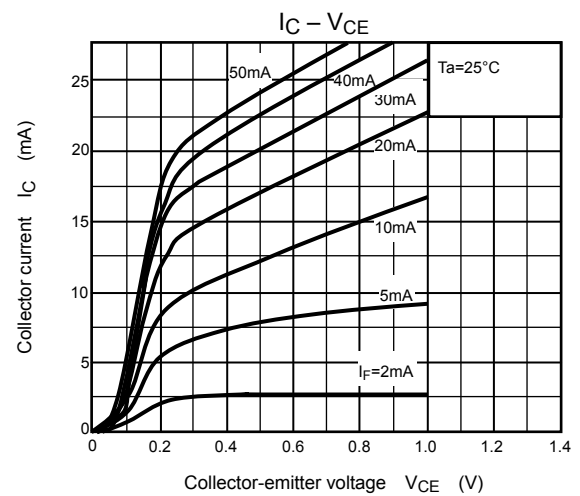
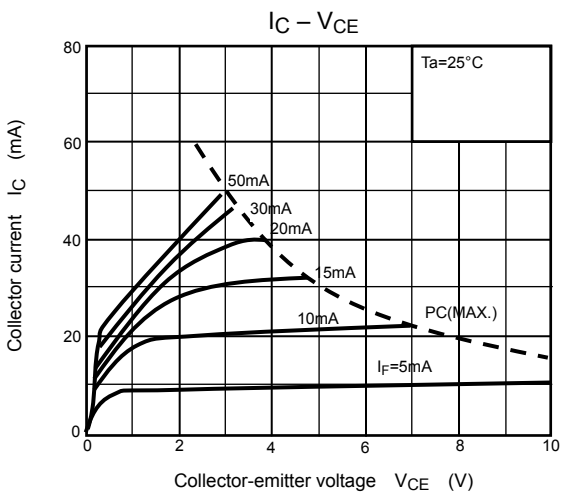
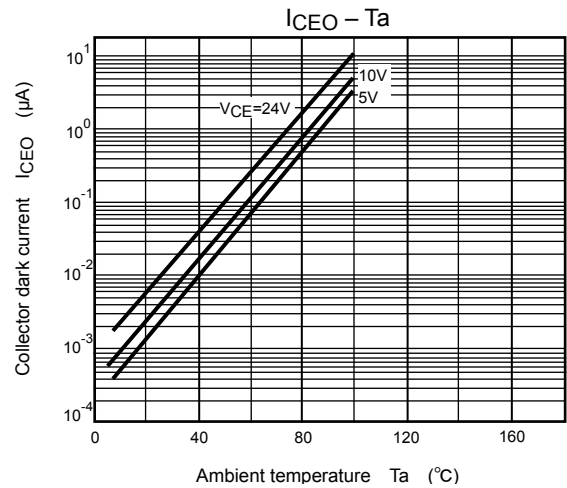
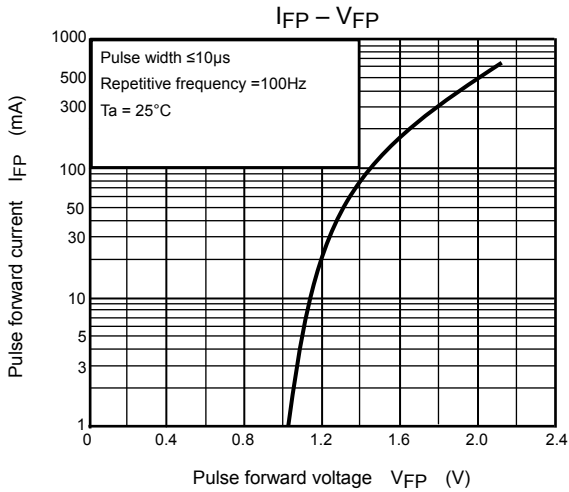
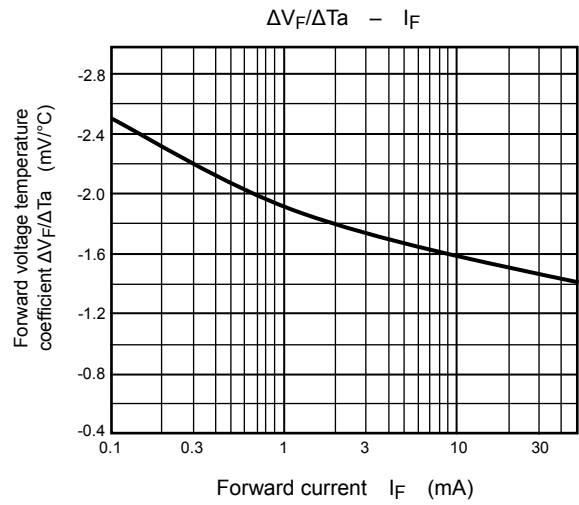
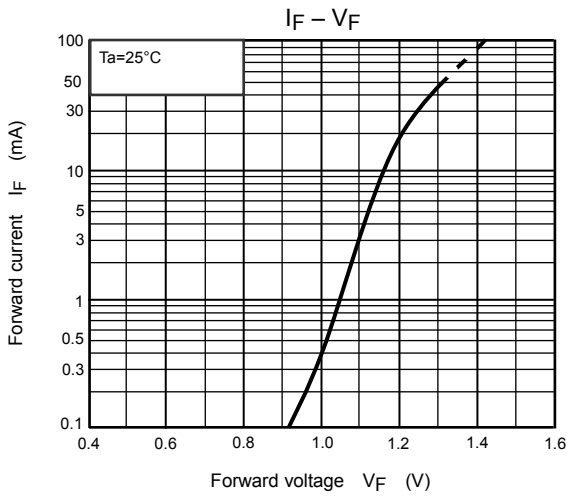
Switching Characteristics (Ta = 25°C)

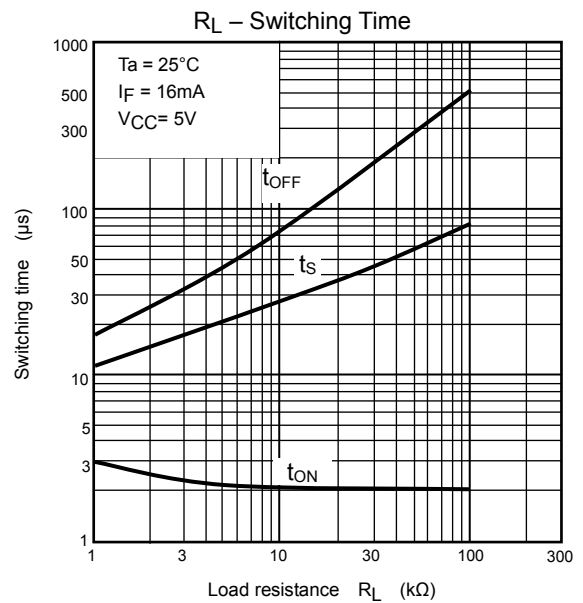
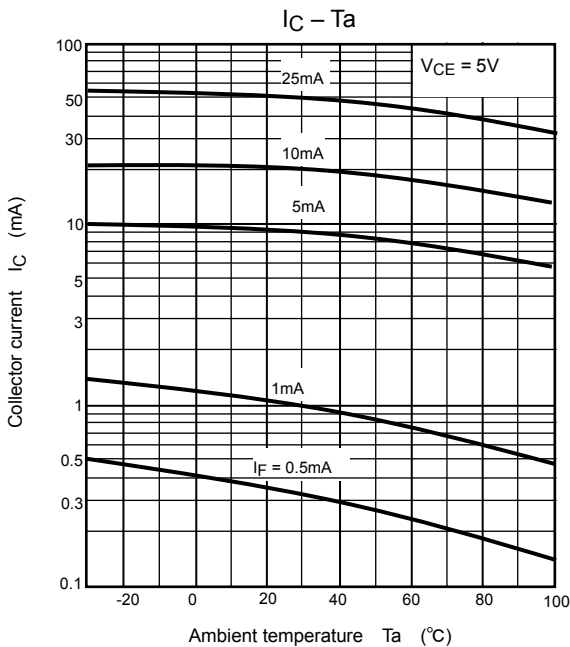
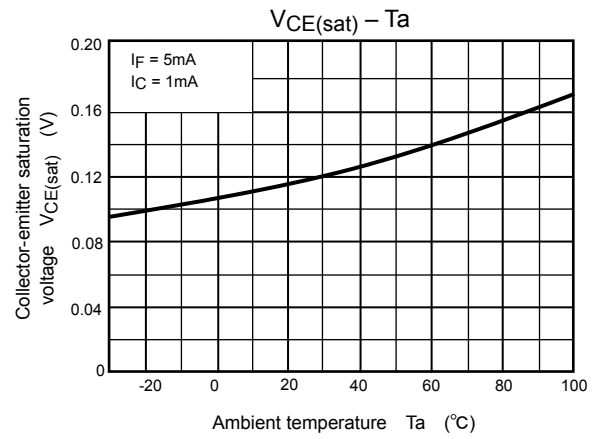
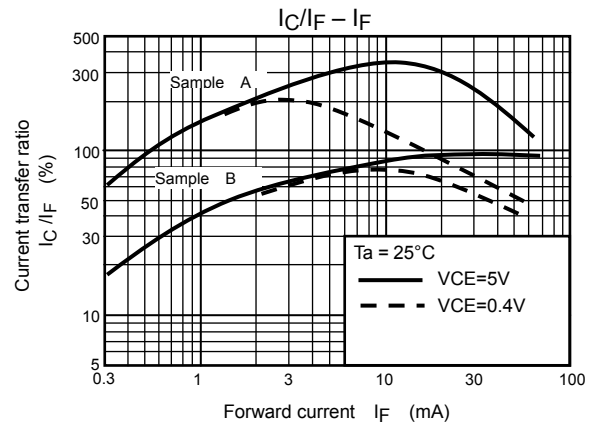
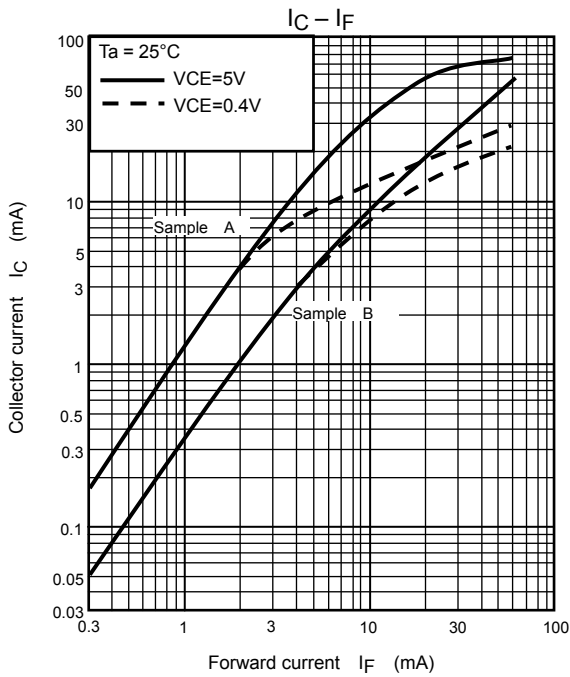
Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Rise time	t_r	$V_{CC} = 10\text{ V}$ $I_C = 2\text{ mA}$ $R_L = 100\Omega$	—	2	—	μs
Fall time	t_f		—	3	—	
Turn-on time	t_{on}		—	3	—	
Turn-off time	t_{off}		—	3	—	
Turn-on time	t_{ON}	$R_L = 1.9\text{ k}\Omega$ (Fig.1) $V_{CC} = 5\text{ V}$, $I_F = 16\text{ mA}$	—	2	—	μs
Storage time	t_s		—	15	—	
Turn-off time	t_{OFF}		—	25	—	

Fig.1 : SWITCHING TIME TEST CIRCUIT









RESTRICTIONS ON PRODUCT USE

20070701-EN

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